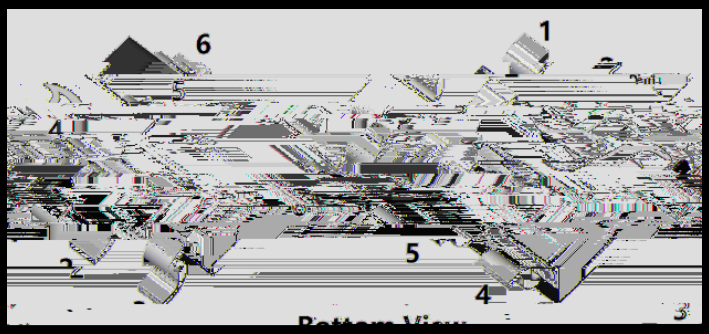
RoHS
COMPLIANT



ie1)
i i $ i $ yNO S(= M

VGS=4.5V) 55 mohm
VGS=2.5V) 75 mohm

ie2)

-20V
-1.5A
VGS=-4.5V) 120 mohm
VGS=-2.5V) 170 mohm

wer LV MOSFET technology
sity Cell Design for Low $R_{DS(ON)}$
ed switching
ith suffix “Q” means AEC-Q101 qualified

g, Logic switch
ch
nagement

	20	-20	V
	10	10	V
	2.0	-1.5	A
	1.3	-1.0	

T_A=100		

238	227	mW
210	220	/ W
-55~+150	-55~+150	

YJJ2429AQ	F2	2429	3000	30000	120000	7“ reel

■ (T_J=25 unless otherwise noted)

Figure1. Output Characteristics

Figure2. Transfer Characteristics

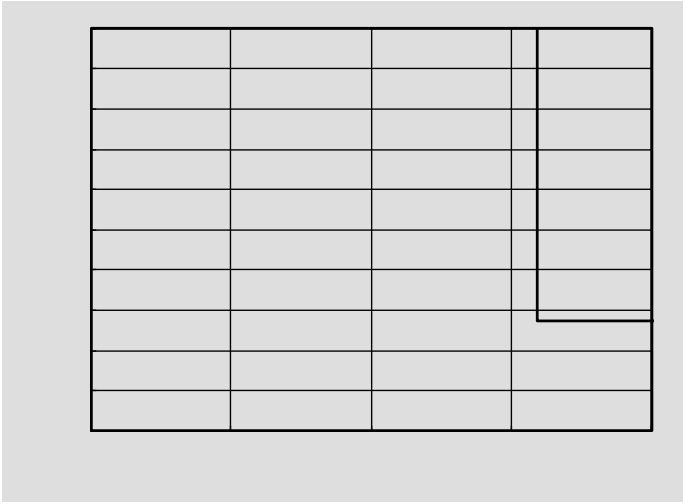


Figure 7. $R_{DS(on)}$ VS Drain Current

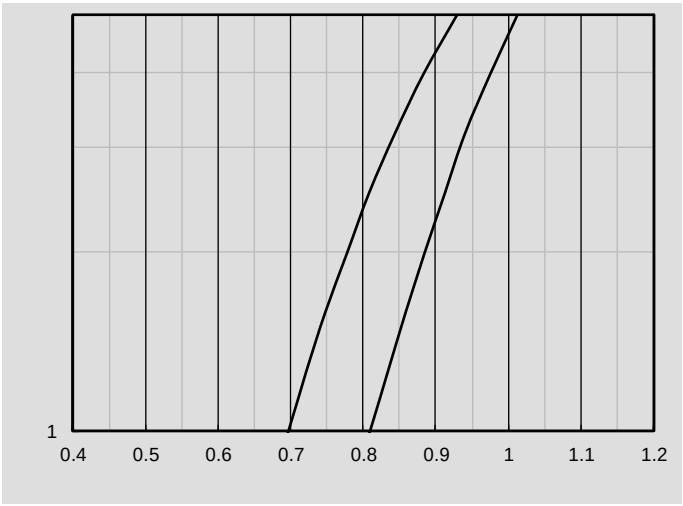
Figure 8. Forward characteristics of reverse diode

Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

Figure 11. Maximum Transient Thermal Impedance

Figure 12. Safe Operation Area



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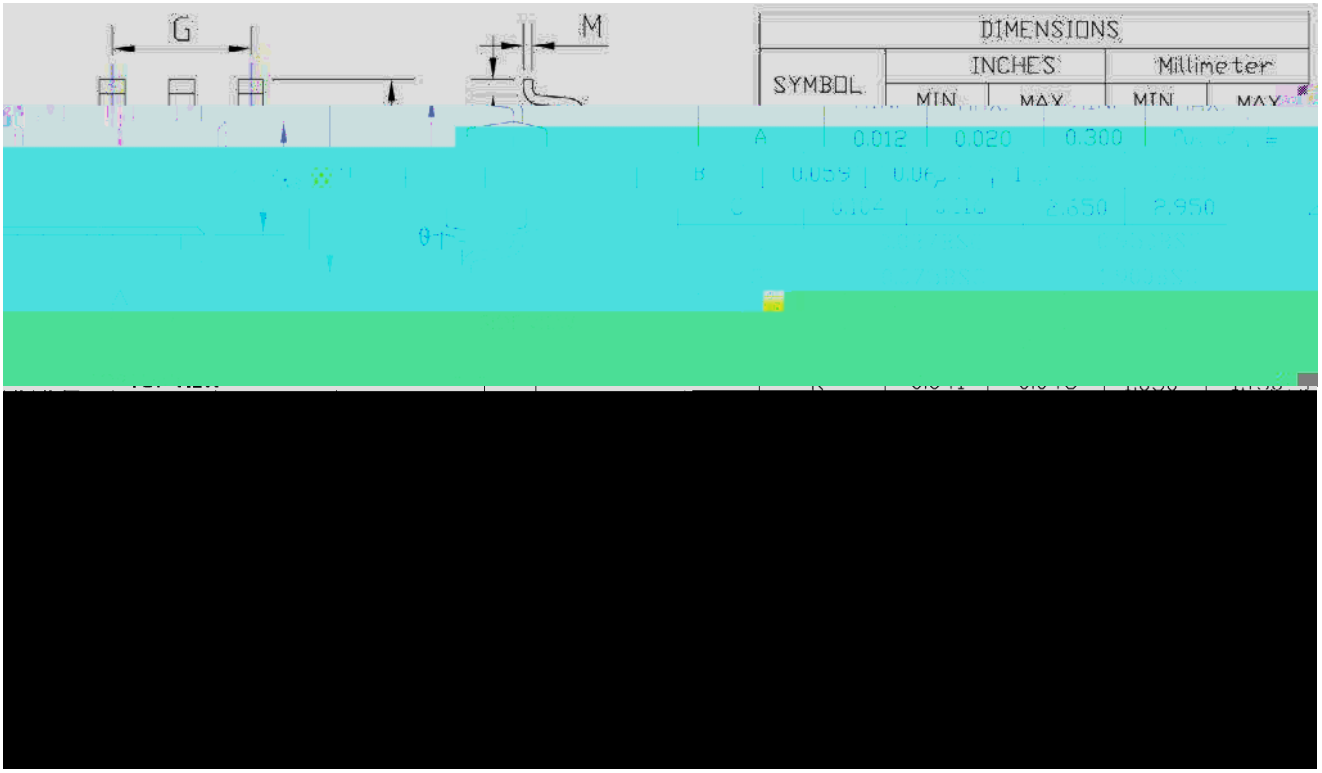
G
M
DIMENSIONS
SYMBOL
INCHES
Millimeter
MIN
MAX
MIN
MAX
A
0.012
0.020
0.300
2.650
2.950

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